

USN

10EC56

## Fifth Semester B.E. Degree Examination, Dec.2015/Jan.2016 Fundamentals of CMOS VLSI

Time: 3 hrs.

Max. Marks:100

Note: 1. Answer FIVE full questions, selecting at least TWO questions from each part.
2. Assume missing data, if any.

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PART - A			
1	a.	Explain with a neat diagram, enhancement mode transistor action of MOS transis	tor.
	b.	Using neat diagram, describe fabrication steps for n-MOS transistor.	(08 Marks)
	c.	Compare CMOS and Bipolar technologies.	(08 Marks) (04 Marks)
2	a.	What do you mean by Lambda ( $\lambda$ ) based design rule? Explain, indicate and draw for PMOS, CMOS and n-mos.	design rule (12 Marks)
	b.	Using CMOS logic draw schematic and Layout diagram for $Y = \overline{AB + CD}$ .	(08 Marks)
3	a.	Explain why p-MOS and n-MOS has been used in CMOS complementary log CMOS complementary logic with an example.	gic. Discuss (06 Marks)
	b.	Describe the following logic structures with an example.	(00 Marks)
		i) Pseudo – n-MOS logic	
		ii) Dynamic CMOS logic	(10 Marks)
	C.	Using Bi-CMOS logic structure design a schematic circuit for $h = \overline{ab + c}$ .	(04 Marks)
4	a.	What is sheet resistance? Derive the expression for sheet resistance.	(08 Marks)
	b.	Explain delay unit.	(06 Marks)
	c.	Discuss the scaling factors for n-MOS transistor.	(06 Marks)
5	0	PART - B	
3	a. b.	Discuss the architectural issues of CMOS subsystem design.	(04 Marks)
	c.	Explain combinational logic using a parity generator.	(08 Marks)
	C.	Explain: i) Dynamic register element ii) Dynamic shift register.	(08 Marks)
6	a.	Design and explain 4bit shifter using 4 × 4 cross bar and barrel shifter.	(12 Marks)
	b.	Explain with a neat diagram 4 – bit serial – parallel multiplier.	(08 Marks)
		paramet manipher.	(00 Marks)
7	a.	Explain with a neat diagram, a three transistor dynamic RAM cell.	(08 Marks)
	b.	Explain CMOS Pseudo – static memory cell using circuit and stick diagram.	(12 Marks)
8	a.		
·	b.	Discuss the floor plan and layout using 4 – bit processor. Write a short note on	(08 Marks)
		i) Built – in – self – test (BIST)	
		ii) Scan design technology.	(12 B/L-1-)
		6-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1	(12 Marks)

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